XP-002278449

AN - 1985-287411 [46]
A - [001] 014 04- 05- 062 229 231 236 246 334 353 38- 39- 524 54& 658 726
AP - JP19840053502 19840322
CPY - TOKE
DC - A89 G06 L03 P83 P84 U11
FS - CPI;GMPI;EPI
IC - G03C1/72 ; G03C5/08 ; G03F7/10 ; H01L21/30
KS - 0207 0231 1304 1306 1307 1995 2016 2805 3295
MC - A06-A00E A12-L02E G06-D04 G06-F03C L03-D03B
- U11-A06
PA - (TOKE ) TOSHIBA KK
PN - JP60198538 A 19851008 DW198546 006pp
PR - JP19840053502 19840322
XA - C1985-124674
XIC - G03C-001/72 ; G03C-005/08 ; G03F-007/10 ; H01L-021/30
XP - N1985-214097
AB - J60198538 Positive resist material includes polycondensate having phenol nucleus and o-nitrobenzyl oxysilane deriv. of formula (I). In (I), R1, R2 and R5 are each H, halo, vinyl, aryl,opt. substd. 1-10C alkyl, 1-10C alkoxy, opt. substd. aryl, aryloxy or siloxy;R4 is H, opt. substd. 1-10C alkyl or phenyl; R5-8 are each H, nitro, cyanine or hydroxy; and p, q and r are integers satisfying relations (1)-(4).
- USE/ADVANTAGE - Resist material of high dry etching resistivity is obtd., with high definition, suitable for UV, partic. for UV exposure.(0/0)
IW - POSITIVE RESIST MATERIAL POLYCONDENSATION PHENOL NUCLEUS ORTHO NITROBENZYL OXY SILANE
IKW - POSITIVE RESIST MATERIAL POLYCONDENSATION PHENOL NUCLEUS ORTHO NITROBENZYL OXY SILANE
NC - 001
OPD - 1984-03-22
ORD - 1985-10-08
PAW - (TOKE ) TOSHIBA KK
TI - Positive resist material - including polycondensate with phenol nucleus and ortho-nitrobenzyl-oxy-silane